

### BD434/436/438

# Medium Power Linear and Switching Applications

• Complement to BD433, BD435 and BD437 respectively



### **PNP Epitaxial Silicon Transistor**

### Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage		
	: BD434	- 22	V
	: BD436	- 32	V
	: BD438	- 45	V
V <sub>CES</sub>	Collector-Emitter Voltage		
	: BD434	- 22	V
	: BD436	- 32	V
	: BD438	- 45	V
V <sub>CEO</sub>	Collector-Emitter Voltage		
	: BD434	- 22	V
	: BD436	- 32	V
	: BD438	- 45	V
V <sub>EBO</sub>	Emitter-Base Voltage	- 5	V
I <sub>C</sub>	Collector Current (DC)	- 4	Α
I <sub>CP</sub>	*Collector Current (Pulse)	- 7	А
I <sub>B</sub>	Base Current	- 1	Α
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	36	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 65 ~ 150	°C

Electrical	Characteristics	T <sub>C</sub> =25°C unless otherwise noted
Electrical	Character istics	I ~=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V <sub>CEO</sub> (sus)	Collector-Emitter Sustaining Voltage					
	: BD434	$I_C = -100 \text{mA}, I_B = 0$	- 22			V
	: BD436		- 32			V
	: BD438		- 45			V
$I_{CBO}$	Collector Cut-off Current	$V_{CB} = -22V, I_{E} = 0$				
	: BD434	$V_{CB} = -32V, I_{E} = 0$			- 100	μΑ
	: BD436	$V_{CB} = -45V, I_{E} = 0$			- 100	μΑ
	: BD438				- 100	μΑ
I <sub>CEO</sub>	Collector Cut-off Current					
	: BD434	$V_{CE} = -22V, V_{BE} = 0$			- 100	μΑ
	: BD436	$V_{CE} = -32V, V_{BE} = 0$			- 100	μΑ
	: BD438	$V_{CE} = -45V, V_{BE} = 0$			- 100	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = -5V, I_{C} = 0$			- 1	mA
h <sub>FE</sub>	* DC Current Gain					
	: BD434/436	$V_{CE} = -5V, I_{C} = -10mA$	40	140		
	: BD438		30	140		
	: ALL DEVICE	$V_{CE} = -1V, I_{C} = -500 \text{mA}$	85	140		
	: BD434/436	$V_{CE} = -1V, I_{C} = -2A$	50			
	: BD438		40			
V <sub>CE</sub> (sat)	* Collector-Emitter Saturation Voltage					
	: BD434	$I_C = -2A$ , $I_B = -0.2A$		- 0.2	- 0.5	V
	: BD436			- 0.2	- 0.5	V
	: BD438			- 0.2	- 0.6	V
V <sub>BE</sub> (on)	* Base-Emitter ON Voltage					
221	: BD434	$V_{CF} = -1V, I_{C} = -2A$			- 1.1	V
	: BD436	1			- 1.1	V
	: BD438				- 1.2	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = - 1V, I <sub>C</sub> = - 250mA	3			MHz

<sup>\*</sup> Pulse Test: PW=300μs, duty Cycle=1.5% Pulsed

# **Typical Characteristics**

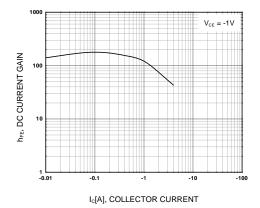


Figure 1. DC current Gain

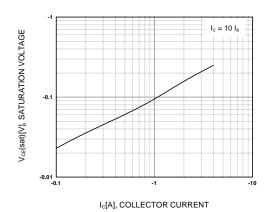


Figure 2. Collector-Emitter Saturation Voltage

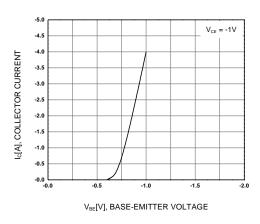


Figure 3. Base-Emitter On Voltage

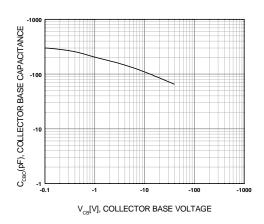


Figure 4. Collector-Base Capacitance

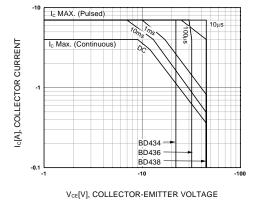


Figure 5. Safe Operating Area

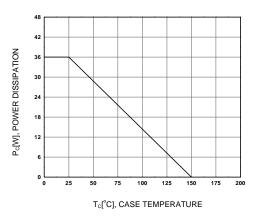
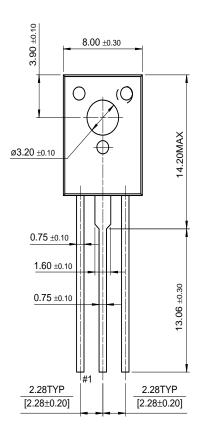


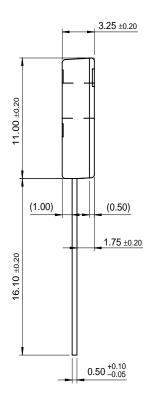
Figure 6. Power Derating

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## **Package Demensions**

TO-126







Dimensions in Millimeters

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